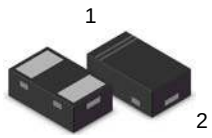
LESD8LU5.0T5G ESD PROTECTION DIODE

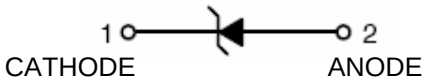
Discription

The LESD8LU5.0T5G is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, digital cameras and many other portable applications where board space is at a premium.

LESD8LU5.0T5G



SOD882



CATHODE ANODE

Applications

- Cellular phones audio
- Digital cameras
- Portable applicationss
- mobile telephone

Features

- Small Body Outline Dimensions: 1.0 mm x 0.6 mm
- Low Body Height: 0.5 mm
- Low Leakage
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- IEC61000−4−2 Level 4 ESD Protection
- These are Pb−Free Devices
- We declare that the material of product compliance with RoHS requirements.

Ordering information

Device	Marking	Shipping
LESD8LU5.0T5G	E5	10000/Tape&Reel

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Air discharge Contact discharge		±15 ±8	kV kV
ESD Voltage Per Human Body Model		16	kV
Total Power Dissipation on FR-5 Board (Note 1) @ T_A=25℃	PD	200	mW
Junction and Storage Temperature Range	TJ,TSTG	-55 to 150	℃
Lead Solder Temperature – Maximum (10 Second Duration)	TL	260	℃

Stresses exceeding Maximum Ratings may damage the device. Maximum Rating are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

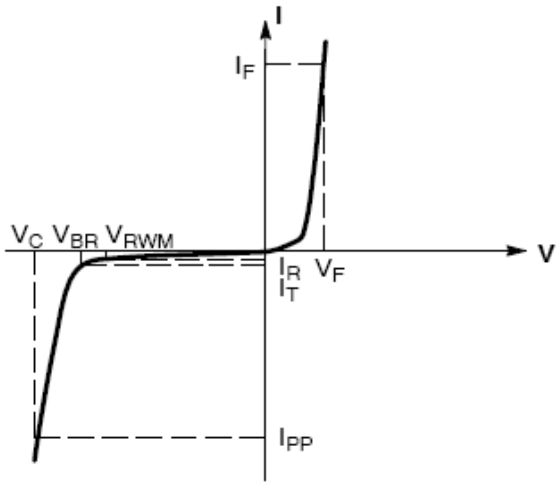
1. FR-5 = 1.0*0.75*0.62 in.

LESD8LU5.0T5G

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_F	Forward Current
V_F	Forward Voltage @ I_F
P_{pk}	Peak Power Dissipation
C	Max. Capacitance @V_R = 0 and f = 1 MHz



Uni–Directional TVS

ELECTRICAL CHARACTERISTICS

Device	V_{RWM} (V)	I_R (μA) @ V_{RWM}	V_{BR} (V) @ I_T (Note 2)	I_T	V_C (V) @ I_{PP} = 1 A (Note 3)	V_C (V) @MAX I_{PP} (Note 3)	I_{PP}(A) (Note 3)	P_{PK}(W) (Note 3)	C (pF)	
	Max	Max	Min	mA	Max	Max	Max	Max	Typ	Max
LESD8LU5.0T5G	5	0.5	6	1.0	10	15	4	60	0.5	0.9

Other voltage available upon request.

2. V_{BR} is measured with a pulse test current IT at an ambient temperature of 25℃

3. Surge current waveform per Figure 1.

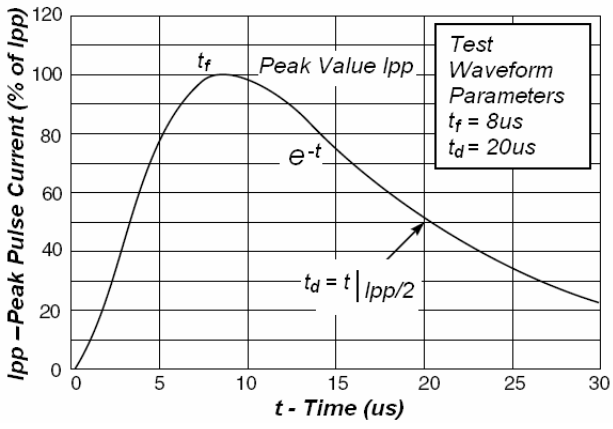


Fig1. Pulse Waveform

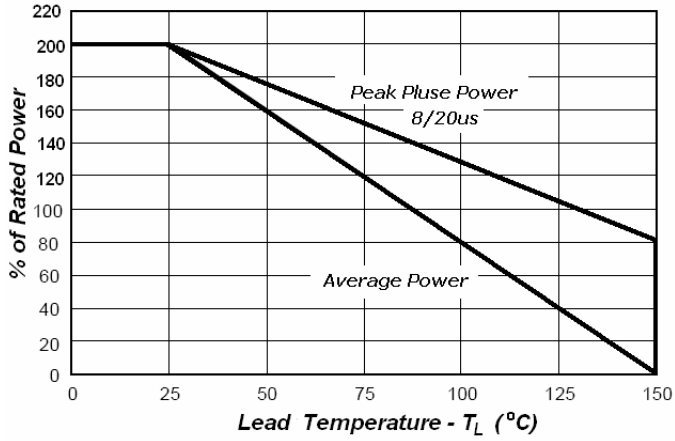
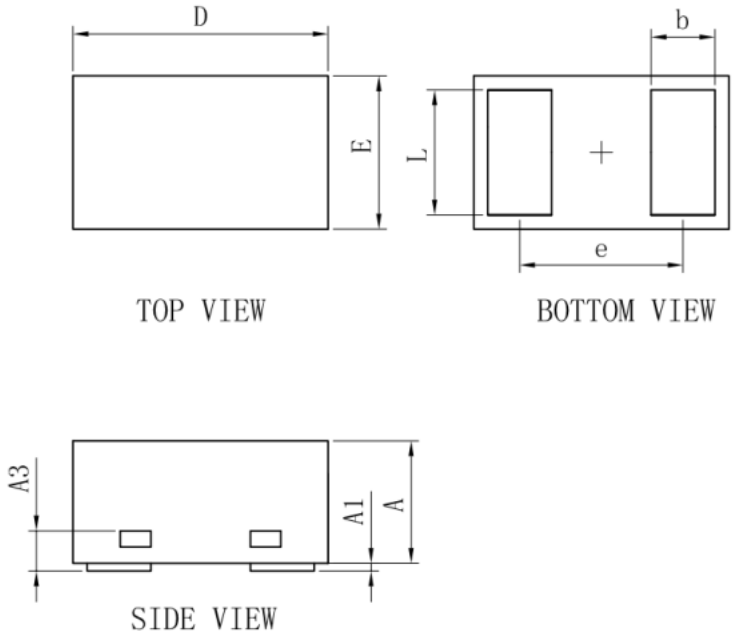


Fig2.Power Derating Curve

LESD8LU5.0T5G

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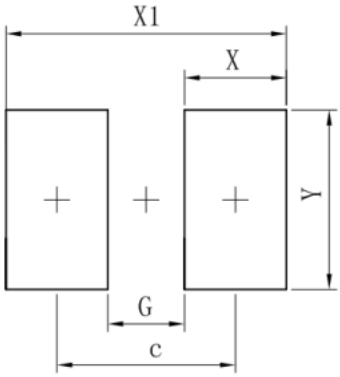
Package Outline Dimension



SOD882			
Dim	Min	Typ	Max
D	0.95	1.00	1.05
E	0.55	0.60	0.65
e	–	0.64	–
L	0.44	0.49	0.54
b	0.20	0.25	0.30
A	0.43	0.48	0.53
A1	0	–	0.05
A3	0.127REF.		
All Dimensions in mm			

Suggested Pad layout

SOD882



Dimensions	(mm)
c	0.70
G	0.30
X	0.40
X1	1.10
Y	0.70

Unikeyic Electronics

Global Electronic Components Distributor

Click to view pricing, inventory, delivery, and lifecycle information:

LRC:

LMBTA13LT1G LUDZS5.6BT1G P6KE150A SZA12A LESD5Z5.0T1G LM5Z3V3T1G LR78M05D
L1SS184LT1G L2N7002FLT1G LM3Z18VT1G LMSZ5252BT1G S-LUDZS3.3BT1G LMBTA92LT1G
LMSZ5243BT1G LTL431APTLT1G S-L1N4148WT1G SZAF5.1A LMBR0520T1G LMSZ5248BT1G
LDTC123JET1G LMSZ5245BT1G SM2100AF LM5Z7V5T1G LMBT4401LT1G L2N7002KWT1G
LM3Z5V6T1G LMBR1100ET1G S-LMSZ5265BT1G L9014QLT1G LMBT4403LT1G